

Spin injection into a short DNA chain

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Quantum spin transport through a short DNA chain connected to ferromagnetic electrodes has been investigated by the transfer matrix method. We describe the system by a tight-binding model where the parameters are extracted from the experimental data and realistic metal energy bands. For ferromagnetic iron electrodes, the magnetoresistance of a 30-basepair Poly(G)-Poly(C) DNA is found to be lower than 10% at a bias of < 4 V, but can reach up to 20% at a bias of 5 V. In the presence of the spin- $\uparrow\downarrow$ mechanism, the magnetoresistance is significantly enhanced when the spin- $\uparrow\downarrow$ coupling is weak but as the coupling becomes stronger the decreasing magnetoresistance develops an oscillatory behavior.

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In recent years, a remarkable progress in direct measurements of electron transport through DNA has generated intense interest in DNA electronics [1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 12, 13]. DNA is found to have diverse electronic properties depending on its structure and the environment around it [6]. The clear semiconductor behavior observed in a short DNA chain of 30-basepair Poly(G)-Poly(C) has been explained by a tight-binding model [2, 9, 11]. On the other hand, spin transport through nanostructures has, of late, been receiving considerable attention because of the possibility of developing spin-based electronic devices [14]. Inspired by the broad interest in spin-injection into mesoscopic systems

[15], we have investigated the quantum spin transport [10] through a short DNA chain connected to ferromagnetic electrodes. We predict an enhancement and oscillation of magnetoresistance in this system taking into account the realistic band structure of ferromagnetic Fe electrode and a spin- $\uparrow\downarrow$ mechanism.

We consider a p-type semiconductor DNA chain of N basepairs connected to a circuit via metal electrodes. The tight-binding Hamiltonian of the system is

$$H = H_d + H_L + H_R + H_{dm} + H_{dps} + H_{sp} \quad (1)$$

where

$$\begin{aligned} H_d &= \sum_{n=1}^N \epsilon_n C_n^\dagger C_n + \sum_{n=1}^{N-1} t_d (C_n^\dagger C_{n+1} + C_{n+1}^\dagger C_n); \\ H_L &= \sum_{n=0}^{N-1} \epsilon_L C_n^\dagger C_n + \sum_{n=0}^{N-1} t_{mL} (C_n^\dagger C_{n+1} + C_{n+1}^\dagger C_n); \\ H_R &= \sum_{n=N}^{N+1} \epsilon_R C_n^\dagger C_n + \sum_{n=N}^{N+1} t_{mR} (C_n^\dagger C_{n+1} + C_{n+1}^\dagger C_n); \\ H_{dm} &= \sum_{n=0}^{N-1} t_{dm} (C_n^\dagger C_1 + C_1^\dagger C_0) + \sum_{n=N}^{N+1} t_{dm} (C_N^\dagger C_{N+1} + C_{N+1}^\dagger C_N); \\ H_{dps} &= \sum_{n=1}^N \epsilon_n (E) C_n^\dagger C_n; \\ H_{sp} &= \sum_{n=1}^N t_d^{so} C_n^\dagger C_n + \sum_{n=1}^{N-1} t_d^s (C_n^\dagger C_{n+1} + C_{n+1}^\dagger C_n); \end{aligned}$$

Here C_n^\dagger is the creation operator of electron with spin \uparrow on site n ($= 1; \dots; N$) of the DNA chain, the left electrode ($n = 0$), and the right electrode ($n = N + 1$). H_d describes electrons (holes) of spin \uparrow in the DNA chain with the on-site energies ϵ_n (ϵ_L), which is equal to the highest occupied molecular orbit (HOMO) energy of each

base-pair, and the hopping parameters t_d between neighboring sites. The HOMO energy band is then determined by ϵ_n and t_d . The Fermi energy E_F in the p-type DNA chain locates between the HOMO and lowest unoccupied molecular orbit (LUMO) bands and is closer to the HOMO band edge. Experimental results have indicated

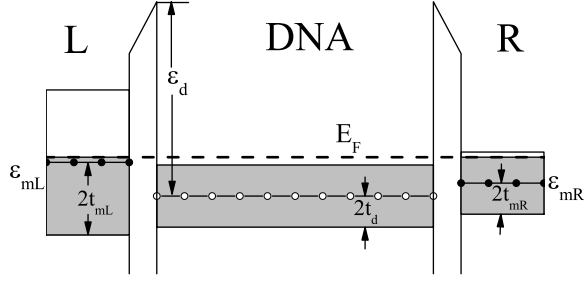


FIG. 1: Energy band of the system in equilibrium.

that the Fermi energy may vary from sample to sample [2]. H_X with $X = L$ or R denotes the Hamiltonian of electrons in the left electrode (L) or the right electrode (R). In the tight-binding model, ϵ_{mX} is the center of the energy band where the electrons are in the metals and $4t_{mX}$ its band width. When the DNA chain contacts to the metal electrodes, exchange of electrons (holes) between the DNA chain and the electrodes becomes possible. In equilibrium, as illustrated in Fig. 1, the Fermi energies of the electrodes and of the DNA match and a tunnelling barrier forms between them. The contact property is described by the tunnelling parameter t_{dm} . When a bias voltage drop is applied over the electrodes, distribution of the voltage drop or the potential profile along the non-equilibrium system depends on the DNA chain property and its contact with the metal electrodes. Since the free electron density in the metals is much higher than that in DNA, we assume that the band structure of the metal electrode is not changed by the applied bias. When the contact between DNA and the electrodes is poor, the voltage drop concentrates on the contact. In case of a perfect contact however, the whole voltage drop should be applied mainly along the DNA chain. In this letter, we assume the voltage drop is on the contact since it is supported by the fit to the experimental result (see below).

In real world, a DNA chain is composed of two strands of bases with one phosphate-sugar backbone connected to each strand. The backbones can affect the on-site energy of electrons in the basepairs. Further, the envi-

ronment around the DNA chain may also play a role in the property of the electrons. Here we use a reservoir of semiconductive chain [9, 16, 17] with a energy band of width 4 and a coupling of strength t_r to each DNA basepair site to mimic the effect of the backbones and the environment. As a result, the on-site energy of each site in the DNA basepair is modified by a self energy $\Sigma_n(E)$ which is energy dependent and is expressed as,

$$\Sigma_n(E) = \frac{t_r^2}{E - \epsilon_r}$$

with ϵ_r being the on-site energy of the semiconductive reservoir chain which we assume to be equal to the DNA on-site energy and $t_r = (E - \epsilon_r) = 2i\sqrt{(E - \epsilon_r)^2 - 4}^{1/2}$ the self energy of any reservoir site which is obtained self-consistently. In what follows, we have used the values $t_r = 0.1$ eV and $t_d = 5$ eV [9]. To study the spin relaxation for a possible spin injection, we introduce the term H_{sp} in the Hamiltonian to take into account the spin flip on-site and between neighboring sites described by the parameters $t_{\uparrow\downarrow}^o$ and $t_{\uparrow\downarrow}^d$ respectively. The spin flip along the DNA can be a result of spin-orbit interaction, magnetic impurity in the backbone, or magnetic environment.

In order to evaluate the transport properties of the system, we have employed the transfer matrix method [4, 5]. For an open system, the secular equation of the system is expressed as a group of infinite number of equations of the form,

$$t_{n-1,n} b_{n-1} + t_{n-1,n}^s b_{n-1} + (\epsilon_n + \Sigma_n(E)) b_n + t_n^{so} b_n + t_{n,n+1} b_{n+1} + t_{n,n+1}^s b_{n+1} = 0;$$

The wave functions of sites $n+1$ and n are related to those of sites n and $n-1$ by a transfer matrix \hat{M} ,

$$\begin{pmatrix} b_{n+1} \\ b_n \end{pmatrix} = \hat{M} \begin{pmatrix} b_n \\ b_{n-1} \end{pmatrix}; \quad (2)$$

with

$$\hat{M} = \begin{pmatrix} t_{n,n+1} & t_{n,n+1}^s & 0 & 0 \\ t_{n,n+1}^s & t_{n,n+1} & 0 & 0 \\ 0 & 0 & 1 & 0 \\ 0 & 0 & 0 & 1 \end{pmatrix} \quad (E - \epsilon_n + \Sigma_n(E)) \begin{pmatrix} t_{n-1,n} & t_{n-1,n}^s \\ t_{n-1,n}^s & t_{n-1,n} \end{pmatrix} \begin{pmatrix} b_{n-1} \\ b_n \end{pmatrix} = 0$$

and $b_{n+1} = (t_{n,n+1})^2 (t_{n,n+1}^s)^2$. Assuming plane wave functions for the electrons $b_n = \frac{1}{\sqrt{L}} (A e^{ik_L n a} +$

$B e^{ik_L n a}$) for $n \leq 0$ and $b_n = \frac{1}{\sqrt{L}} (C e^{ik_L n a} + D e^{ik_L n a})$ for $n \geq N+1$ in the left and right electrodes respectively, we can express the output wave amplitude C in terms of the

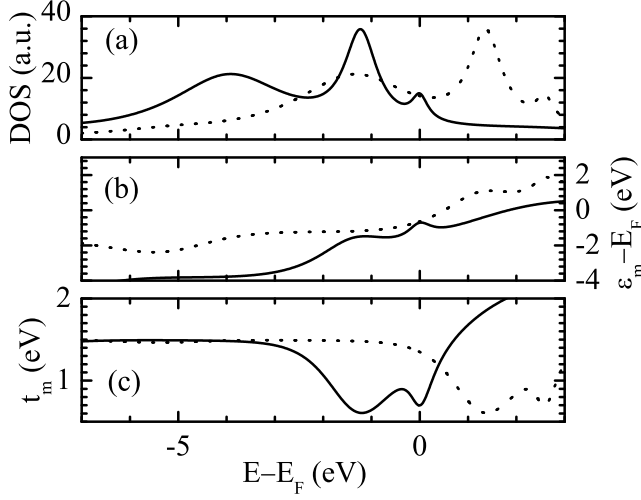


FIG. 2: Energy dependence of the parameters t_m (b) and t_m (c) for ferromagnetic Fe. Solid curves and dotted curves correspond to spin-up and spin-down electrons. The resulting bulk DOS is also shown in (a).

input wave amplitude A and the transmission,

$$T(E) = \frac{4A^2 \sin^2(k_R a)}{4A^2 \sin^2(k_L^+ a) + 4A^2 \sin^2(k_L^- a)};$$

We choose a normalized incident amplitude $A = 1 = \sin(k_L a)$. The net current primarily comes from transmission of electrons of energy between the electrodes' Fermi energies and is calculated as [17]

$$I = \frac{e^2}{h} \sum_1^Z \int_{-1}^1 dE T(E) [f_L(E) - f_R(E)]$$

with the Fermi function $f(E) = 1/\exp[(E - E_F)/k_B T]$ and the room temperature $T = 300$ K. For ferromagnetic electrodes the magnetoresistance is defined as the percentage change of resistance between parallel and anti-parallel configurations $R_m = (R_{\text{anti}} - R_{\text{para}})/R_{\text{para}} = (I_{\text{para}} - I_{\text{anti}})/I_{\text{para}}$.

In metals, an electron of energy E may come from different energy bands. The corresponding effective parameters t_m and t_m are then an average of the parameters of these bands and are energy dependent. In linear or quasi-equilibrium system, they are approximately the values near the Fermi energy. In a non-equilibrium system, if the difference of the Fermi levels between the two electrodes is comparable to the energy band width of the metals, the energy dependence should be taken into account. In the existing experiments the applied bias can be higher than 4 eV, which is larger than the width of the d bands where the Fermi level locates in many metals. In the case of Ferromagnetic Fe which exemplifies the electrode material here, approximately five bands can be identified from the density of states (DOS)

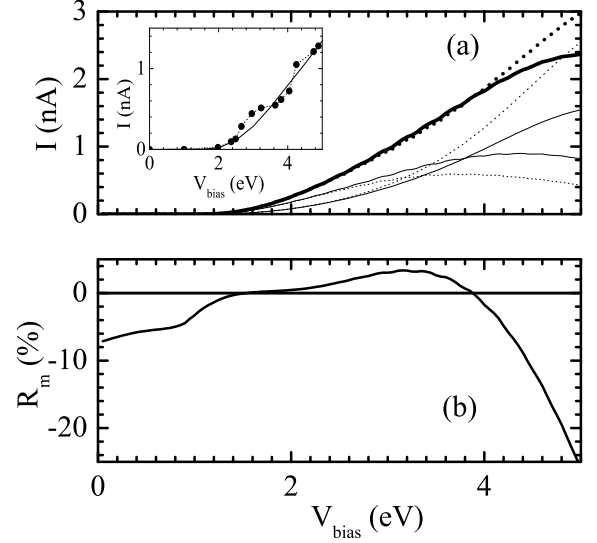


FIG. 3: (a) The I-V curve of a 30-basepair Poly(G)-Poly(C) DNA between two ferromagnetic Fe electrodes of parallel (solid curves) and anti-parallel (dotted) configurations. The thicker curves illustrate the total currents and the thinner ones the contribution from the two spin branches. (b) The magnetoresistance versus the applied bias potential. In the inset of (a), we show our theoretical t (thick solid curve) to the experimental result (filled circles connected by dotted lines) in Ref. [2].

near the Fermi energy of the bulk material [18]. For the spin-up (majority) electrons, the five bands locate approximately at 2.5, 0, 0.68, 3.4, and 7 eV above the Fermi energy with band width 6, 0.3, 0.6, 4.1, and 3.7 eV respectively. For the spin-down (minority) electrons, the energy bands are the same as above but shifted 2.58 eV to higher energy. Using Lorentzian broadening, we can mimic the bulk DOS and extract the parameters t_m and t_m as shown in Fig. 2. At the Fermi energy, we get the hopping parameters 0.39 eV and 1.62 eV for spin-up and spin-down electrons respectively which coincide with the result obtained from the Fermi velocity [10].

Just as in Ref. [9], we extract the parameters of the DNA chain by fitting the experimental result of Ref. [2]. By evaluating the energy-dependent parameters t_m and t_m from Platinum's band structure [19], we can fit the experimental result as shown in the inset of Fig. 3(a). As a result, we find that the hopping parameter is $t_d = 0.6$ eV, the equilibrium Fermi energy is 1.73 eV higher than the DNA HOMO on-site energy, the contact parameters are $t_{dm} = 0.019$ eV for the right electrode and 0.013 eV for the left, 1/3 of the bias voltage drop at the right contact and 2/3 at the left. The above parameters are close to those obtained in Ref. [9] except for a larger t_{dm} in the present case.

For ferromagnetic Fe electrodes as shown in Fig. 3(a), we get two I-V curves corresponding to the parallel (solid curves) and anti-parallel (dotted curves) magnetization

